



# Aliovalent co-doping and annealing effect on photoluminescence and scintillation properties of $\text{Lu}_3\text{Al}_5\text{O}_{12}:\text{Ce}^{3+}$ epitaxial films

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# Outline

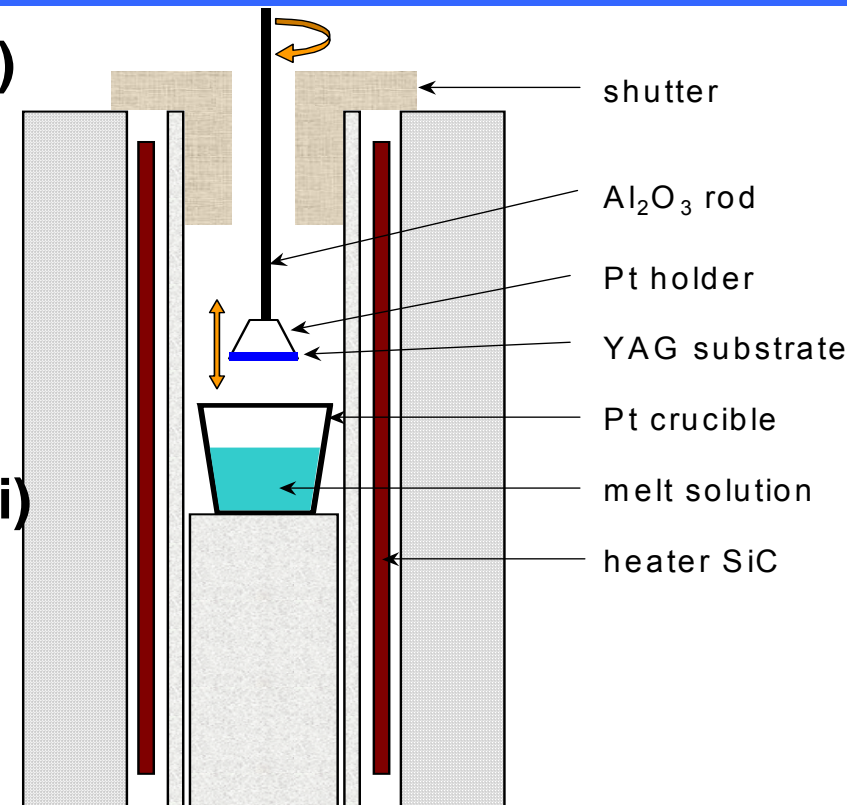
- Motivation – Ce<sup>3+</sup> doped Lu<sub>3</sub>Al<sub>5</sub>O<sub>12</sub> garnets – Aliovalent co-doping and annealing effect
- Experimental section
- Results & Discussion
  - Absorption
  - PL Excitation & Emission
  - PL Decay
  - Radioluminescence
  - Alpha Decay
- Conclusions

# Motivation

- Scintillation materials have thundering applications in the field of high-energy physics, medical imaging, geological exploration, homeland security *etc.*
- Ce<sup>3+</sup> doped garnets are good scintillators due to their less point defects and traps, large band gap, high chemical and thermal stability, high density, broad transmission range.
- The aliovalent co-dopants (Mg<sup>2+</sup>, Ca<sup>2+</sup> *etc.*) could alter the point defect structure, reduces the rise and decay times, and suppresses the charge carrier trapping on defect sites. The Si<sup>4+</sup> co-doping would give interesting results.
- Annealing the Mg<sup>2+</sup>/Ca<sup>2+</sup> rich Ce<sup>3+</sup> doped garnets in reducing atmosphere at higher temperatures would give exciting results.
- The liquid phase epitaxy is a unique technique for the growth of high quality single crystalline films with minimal concentration of the vacancy- and antisite-related defects.

# Experimental work

- Growth technique: **Liquid phase epitaxy (LPE)**
- Used fluxes: **BaO – B<sub>2</sub>O<sub>3</sub> – BaF<sub>2</sub>**
- Growth temperature: **~1030 °C**
- Growth rate: **~0.12 μm/min**
- Composition» **Ce<sub>0.02</sub>Lu<sub>2.98</sub>Al<sub>5</sub>O<sub>12</sub>:X**  
**[X=Mg(0-7000 ppm), Ca (0-6000 ppm), Ca+Si)**
- Thickness of grown films: **30-12 μm**



**Absorption:** Specord 250, range: 190-1100 nm

**Excitation & Emission:** Horiba JY Fluoromax 3

**Radioluminescence:** Custom made spectrofluorometer 5000M,  
Horiba Jobin Yvon using an X-ray tube (10 kV, 50 mA)

**PL Decay:** Spectrofluorometer 5000M , nanoLED, Hamamatsu R7207-01 and  
Tektronix TDS3052C digital Phosphor Oscilloscope

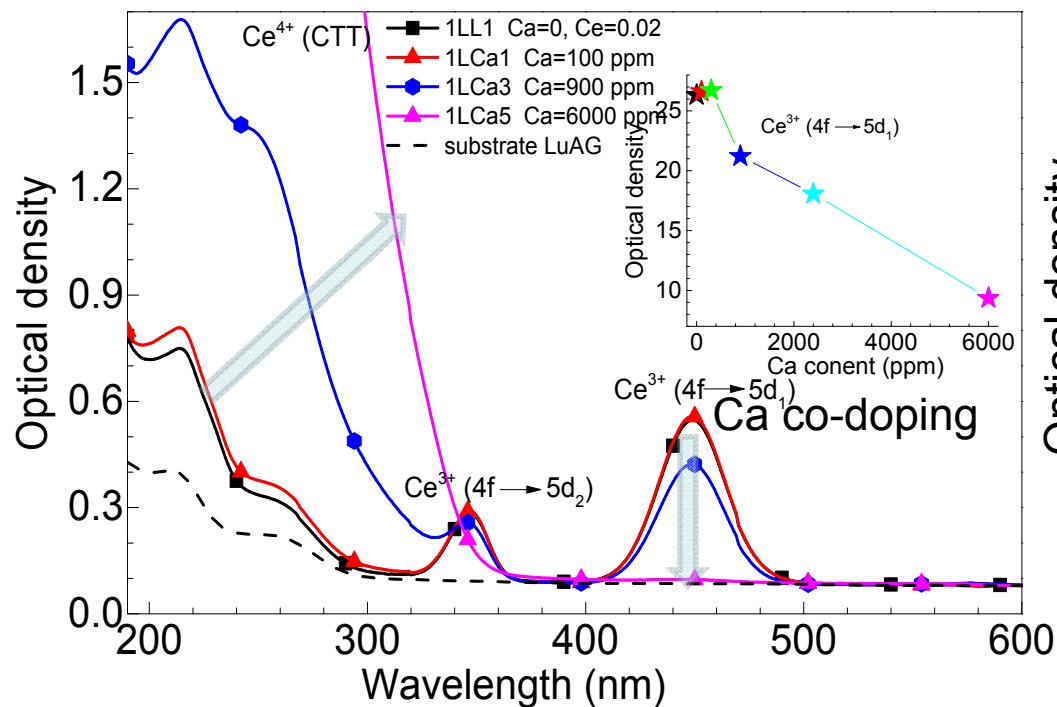
**Alpha decay:** Source- <sup>241</sup>Am, 5 mV

**Annealing:** 1100 °C, 10 hrs, reducing atmosphere Ar: 5%H<sub>2</sub>

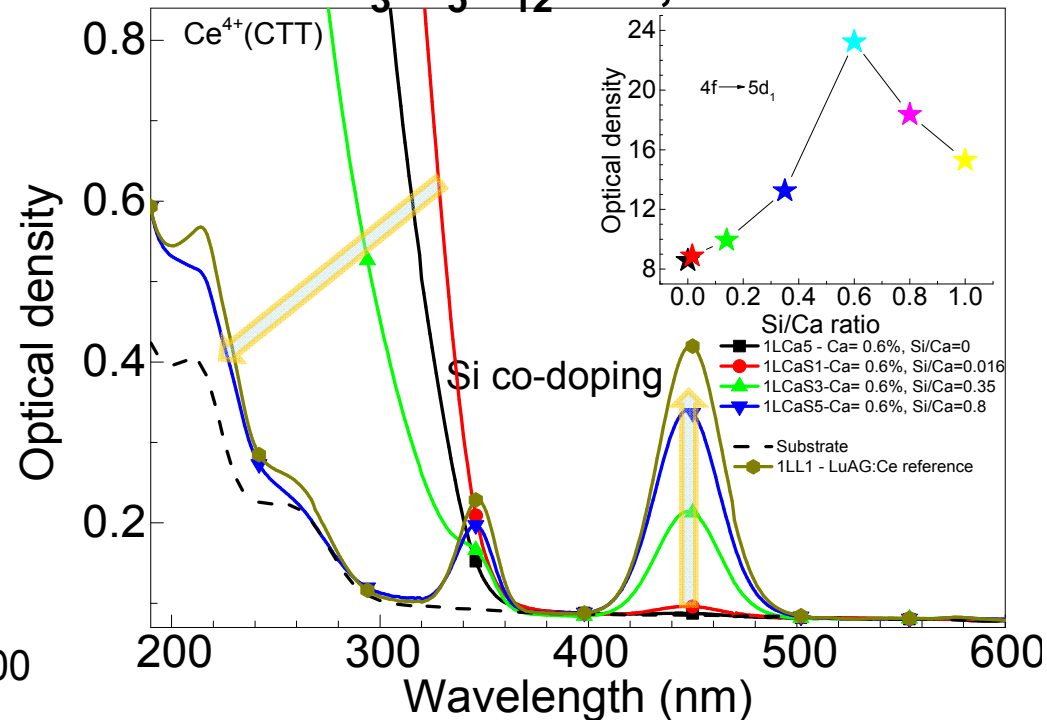
# **Results & Discussion**

# Absorption

## Lu<sub>3</sub>Al<sub>5</sub>O<sub>12</sub>: Ce, Ca

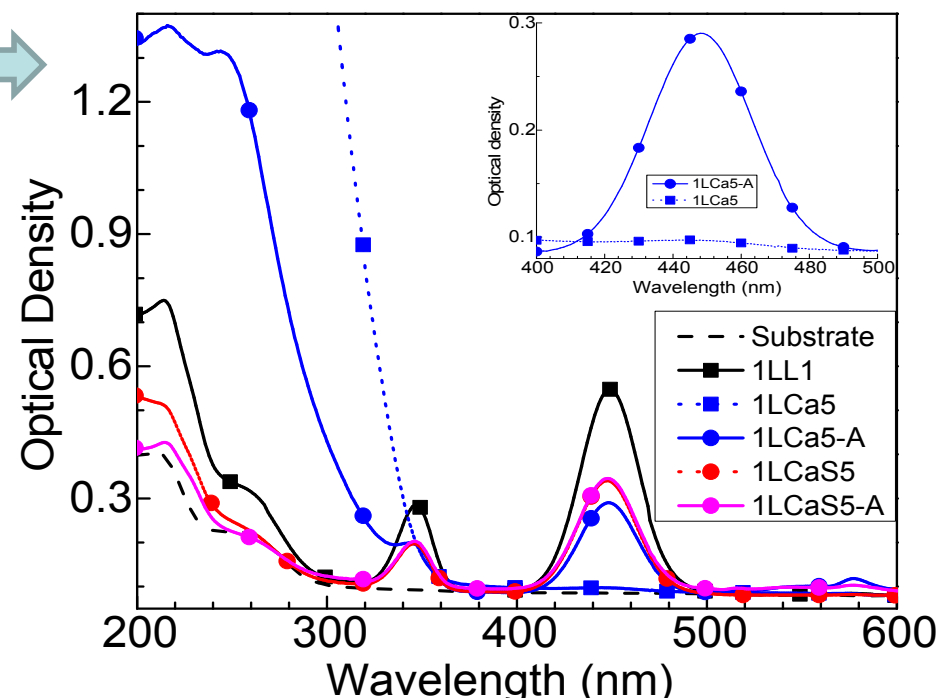


## Lu<sub>3</sub>Al<sub>5</sub>O<sub>12</sub>: Ce, Ca+Si



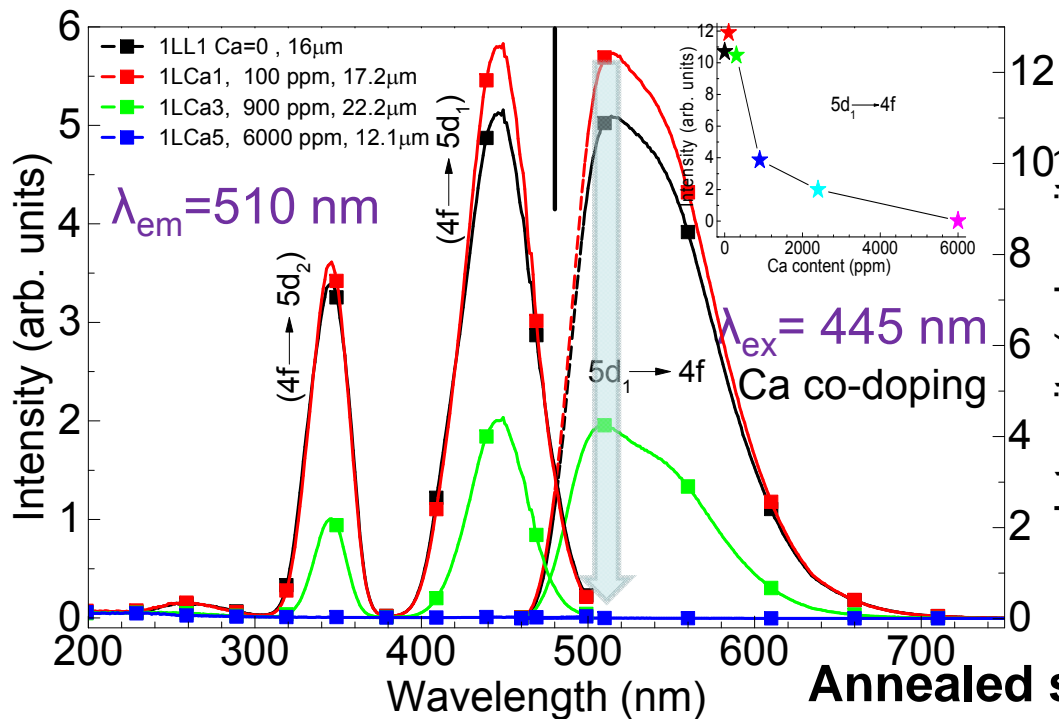
## Annealed samples

- The charge transfer transition (CTT):  
 $O^{2-} (2p) \rightarrow Ce^{4+} (4f)$
- The diminishing in the visible region is due to valence change of Ce<sup>3+</sup> into Ce<sup>4+</sup>
- Similar trend was also observed in Mg<sup>2+</sup> codoped LuAG films

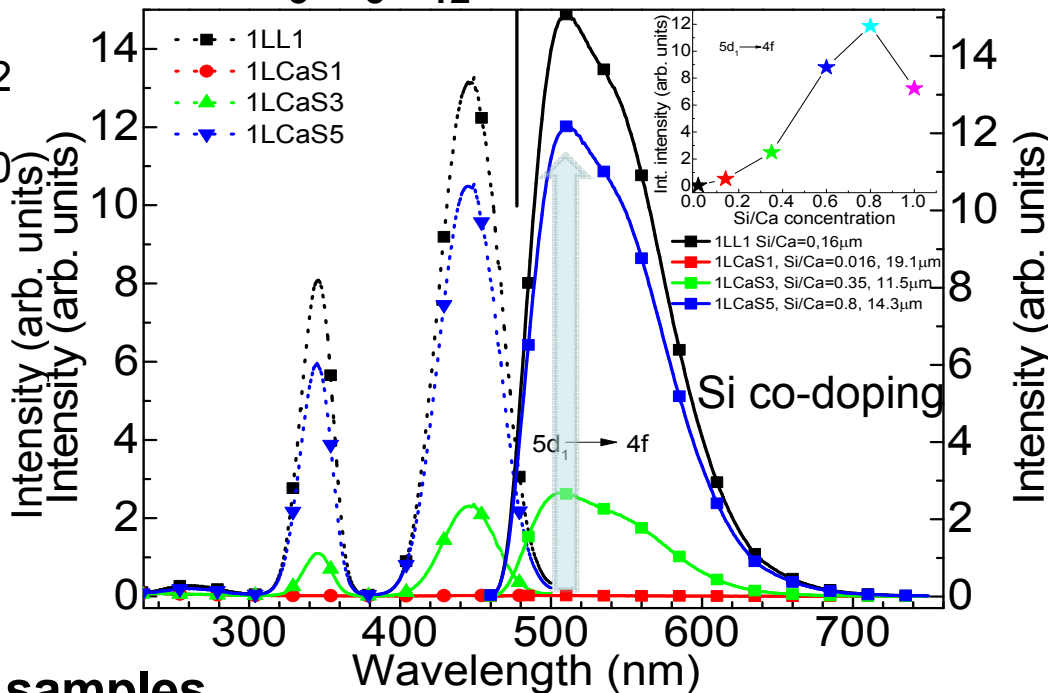


# Excitation & Emission

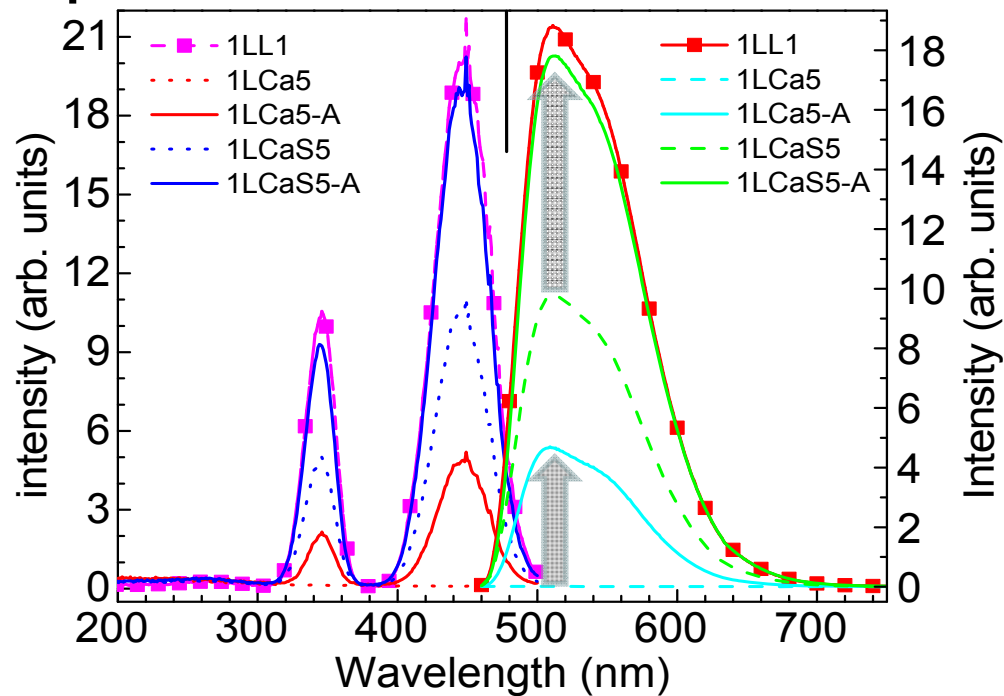
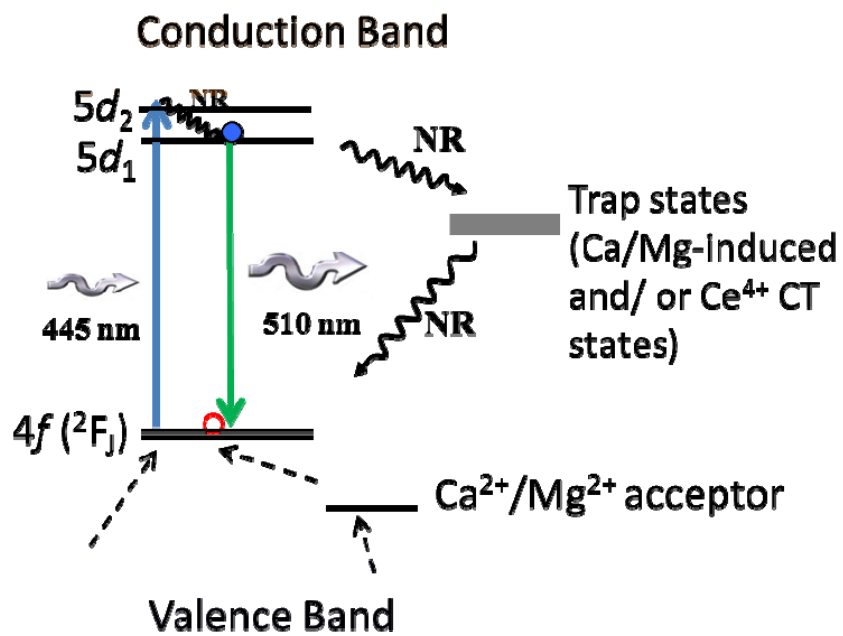
**Lu<sub>3</sub>Al<sub>5</sub>O<sub>12</sub>: Ce, Ca**



**Lu<sub>3</sub>Al<sub>5</sub>O<sub>12</sub>: Ce, Ca+Si**

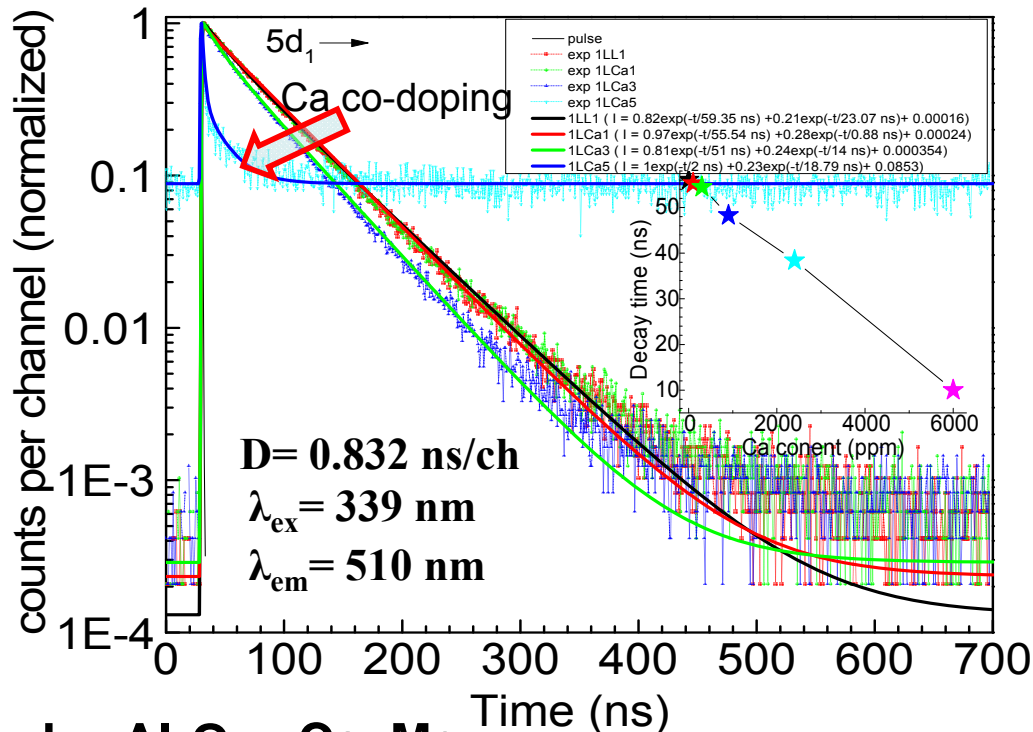


**Annealed samples**

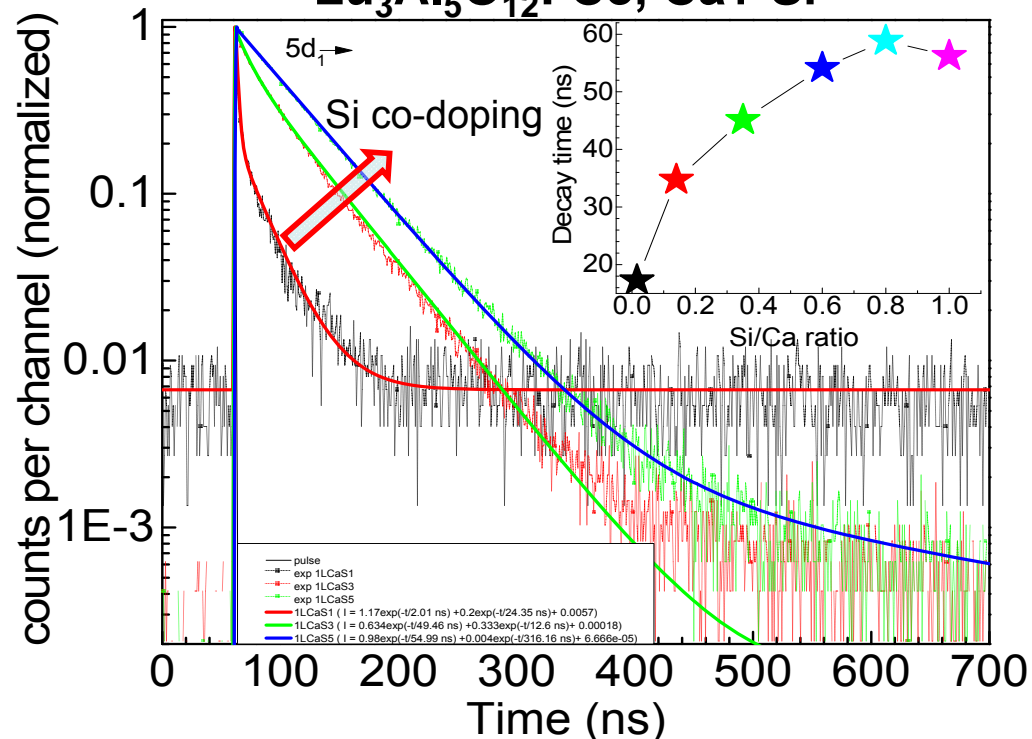


# PL Decay

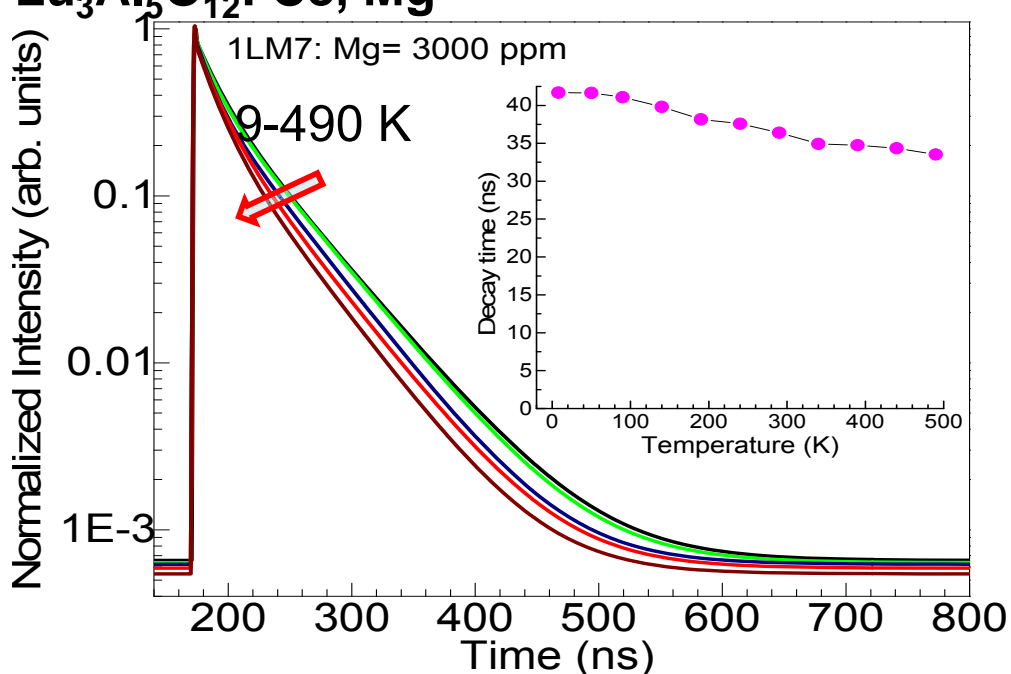
## Lu<sub>3</sub>Al<sub>5</sub>O<sub>12</sub>: Ce, Ca



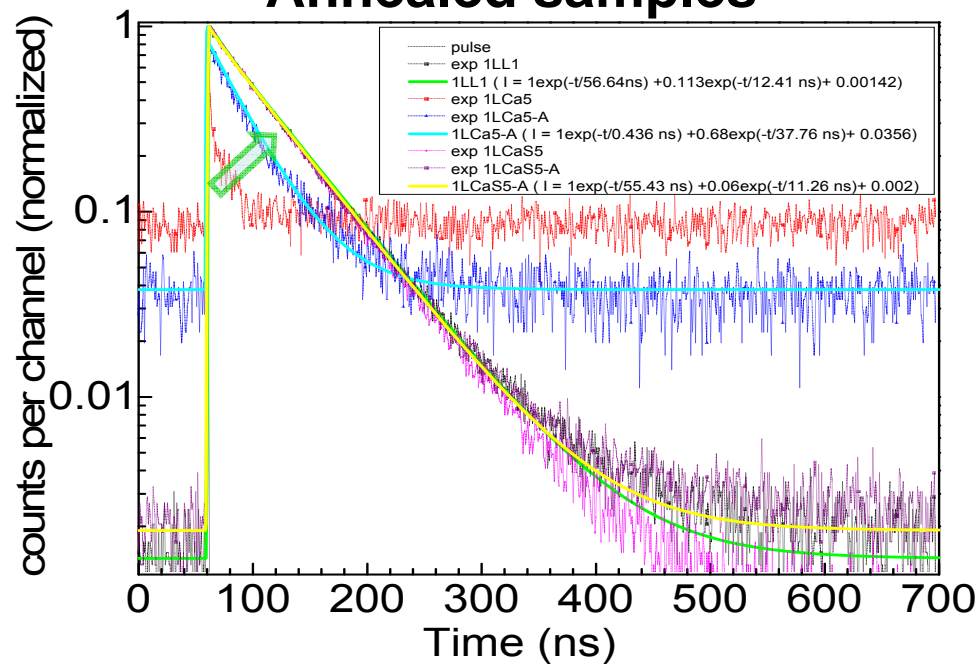
## Lu<sub>3</sub>Al<sub>5</sub>O<sub>12</sub>: Ce, Ca+ Si



## Lu<sub>3</sub>Al<sub>5</sub>O<sub>12</sub>: Ce, Mg

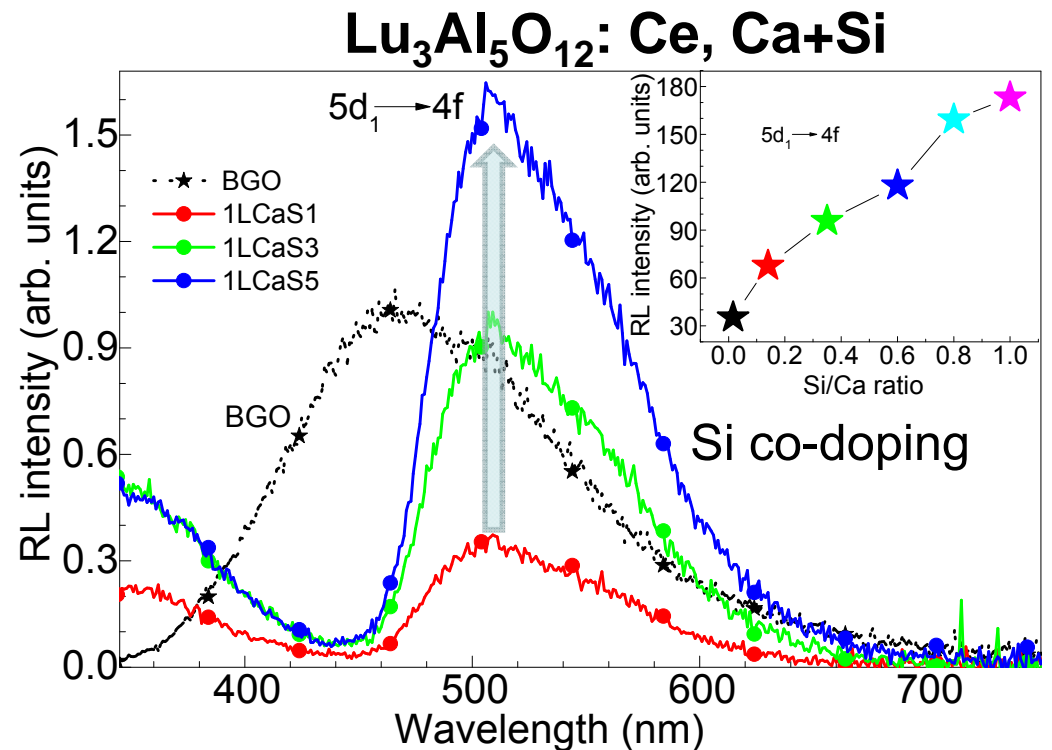
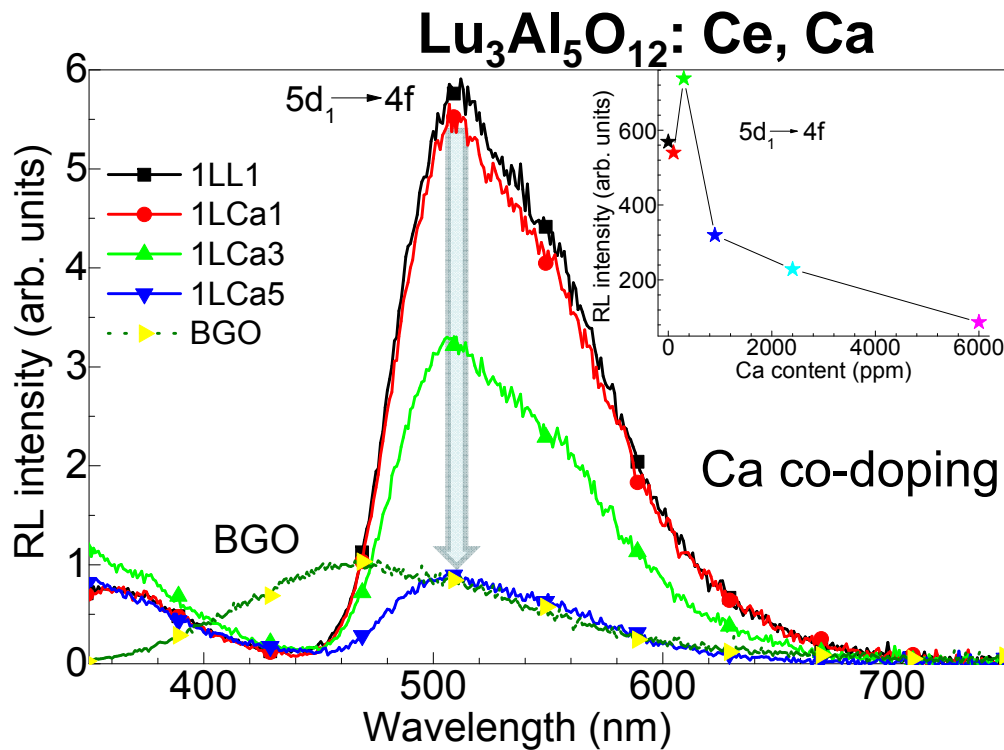


## Annealed samples



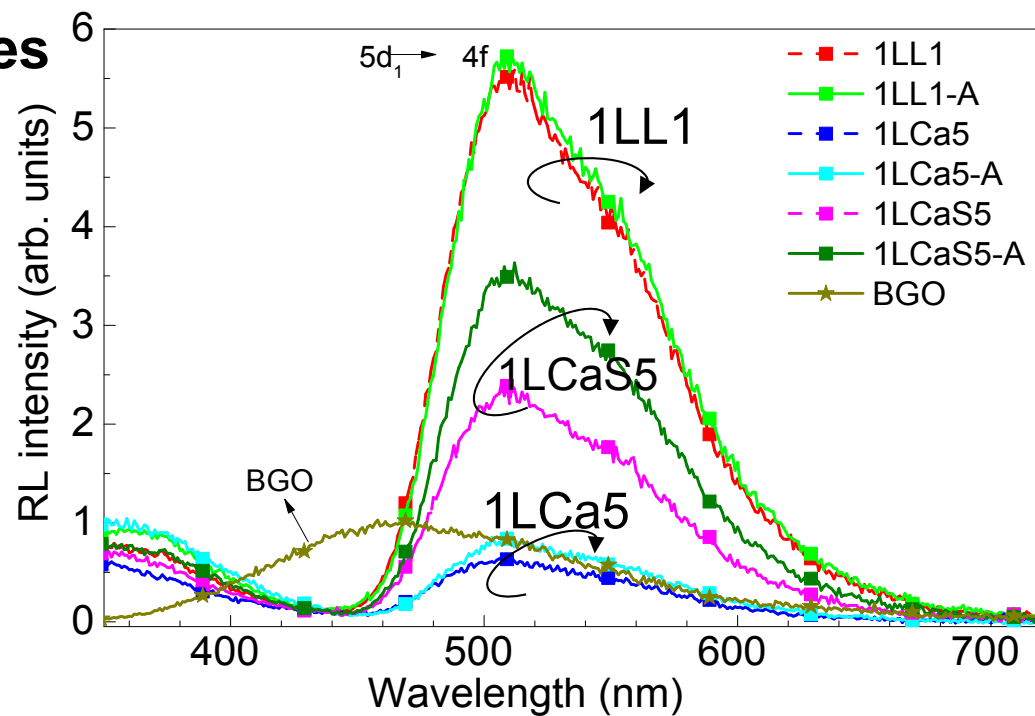


# Radioluminescence



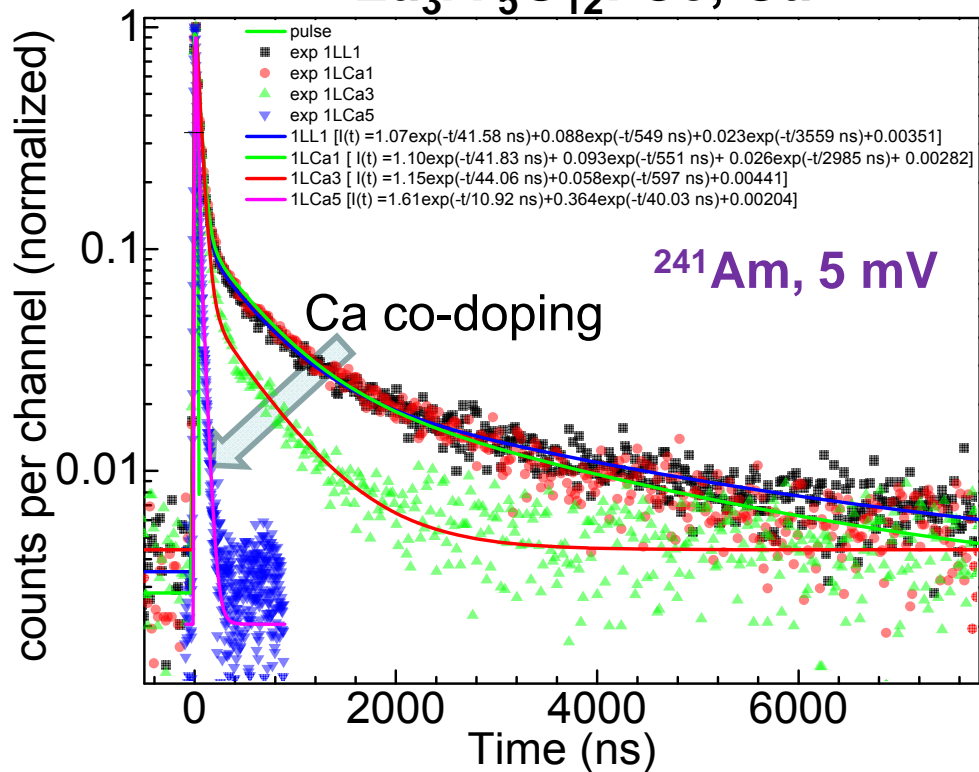
## Annealed samples

Power = 10 kV, 50 mA

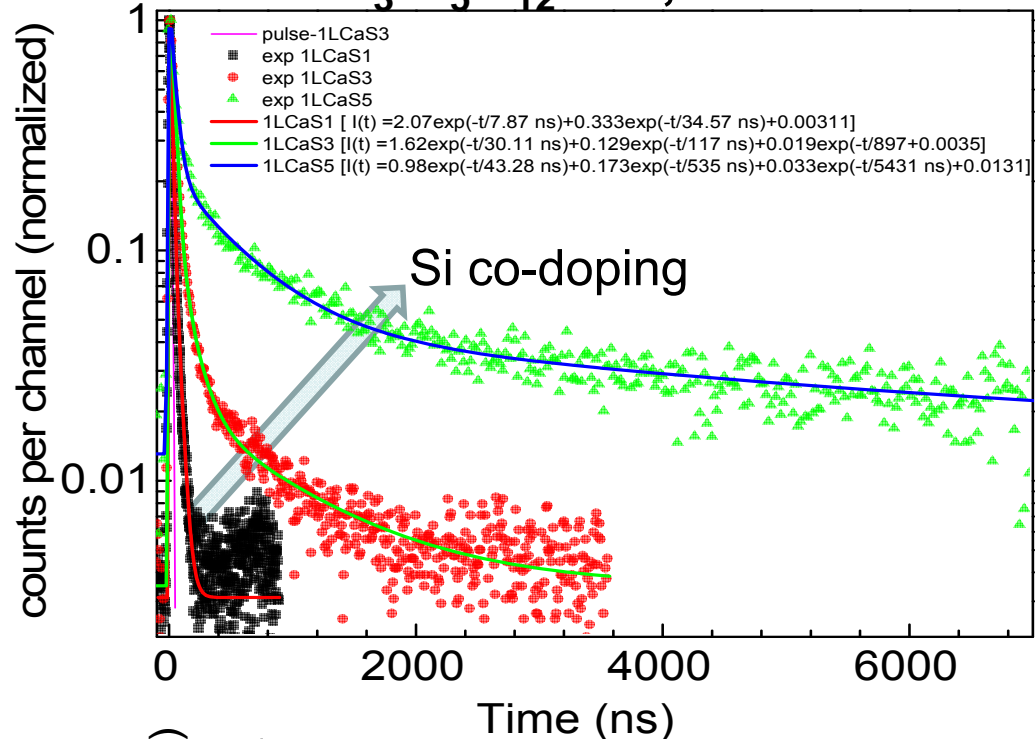


# Alpha decay

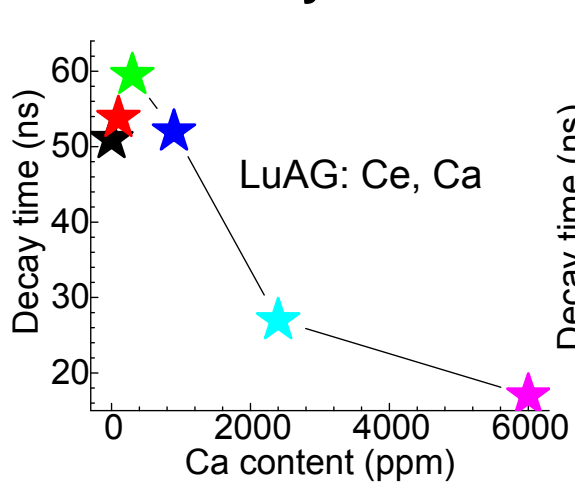
## Lu<sub>3</sub>Al<sub>5</sub>O<sub>12</sub>: Ce, Ca



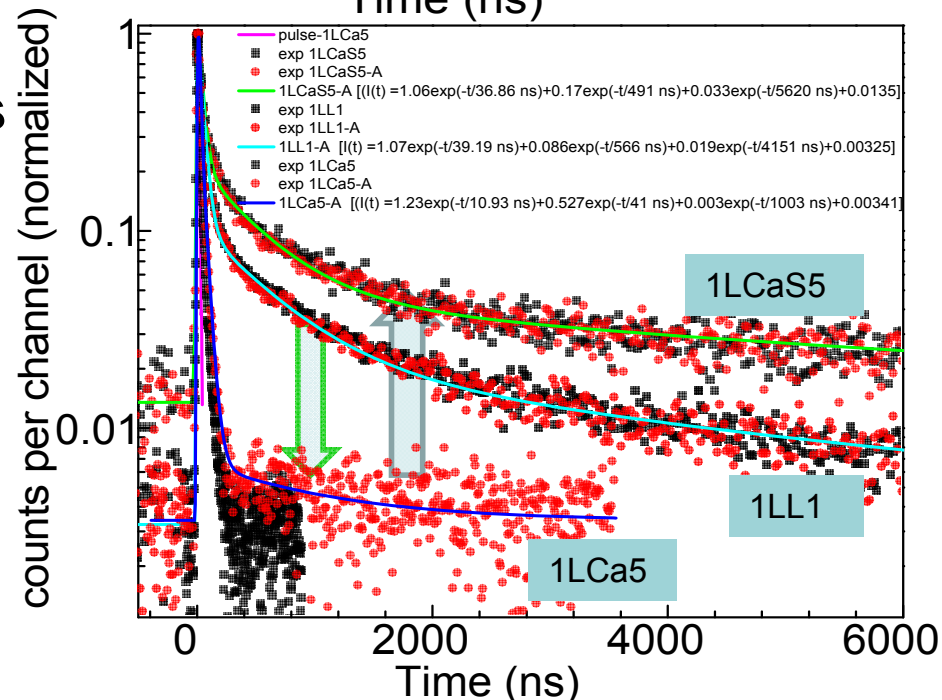
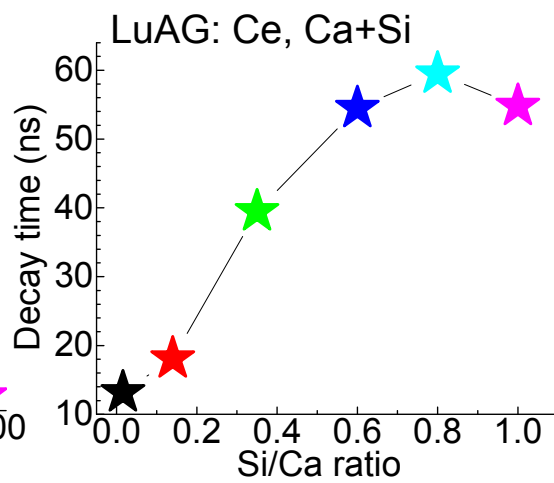
## Lu<sub>3</sub>Al<sub>5</sub>O<sub>12</sub>: Ce, Ca+Si



### Mean decay time



### Annealed samples



# Conclusions

- Aliovalent ( $\text{Mg}^{2+}$ ,  $\text{Ca}^{2+}$ ,  $\text{Si}^{4+}$ ) co-doped  $\text{Lu}_3\text{Al}_5\text{O}_{12}:\text{Ce}^{3+}$  epitaxial films have been prepared by liquid phase epitaxy technique.
- The absorption results indicate that at high  $\text{Mg}^{2+}$  or  $\text{Ca}^{2+}$  co-doping, all the  $\text{Ce}^{3+}$  ions tend to convert into  $\text{Ce}^{4+}$  ions due to change of valence. Upon adding  $\text{Si}^{4+}$  ions into the highly  $\text{Ca}^{2+}$  co-doped  $\text{Lu}_3\text{Al}_5\text{O}_{12}:\text{Ce}^{3+}$  films, the  $\text{Ce}^{3+}$  ions have been re-established due to charge compensation.
- Intense visible emission is observed from low  $\text{Mg}^{2+}$  or  $\text{Ca}^{2+}$  co-doped  $\text{Lu}_3\text{Al}_5\text{O}_{12}:\text{Ce}^{3+}$  films, excited at 445 nm. At high  $\text{Ca}^{2+}$  co-doping, the emission gets quenched, but  $\text{Si}^{4+}$  addition could regenerate the visible emission.
- At low  $\text{Mg}^{2+}$  or  $\text{Ca}^{2+}$  content, the decay curves are found slightly non-exponential with mean decay time around 55 ns.
- After annealing the highly  $\text{Ca}^{2+}$  co-doped  $\text{Lu}_3\text{Al}_5\text{O}_{12}:\text{Ce}^{3+}$  films at 1100 °C in reducing atmosphere, part of the  $\text{Ce}^{4+}$  ions were converted into  $\text{Ce}^{3+}$  ions.

Thank you